

Battery Charge Front-End Full Protection

General Description

The HM9519 provides complete Li+ charger protection against Input over-voltage, input over-current and thermal shutdown protection is also available. When any of the monitored parameters is over the threshold, the IC turns off the charging current. All protections also have deglitch time against false triggering due to voltage spikes or current transients. The system is positive overvoltage protected up to +30V. Thanks to a very low current consumption, the USB charge is compatible with this integrated component.

The HM9519 provides complete Li+ charger protections, and saves the external MOSFET and Schottky diode for the charger of cell phone's PMIC. This device uses internal PMOS FET, making external devices unnecessary, which reduces the system cost and PCB area of the application board. The above features and small package make the HM9519 an ideal part for cell phones applications. HM9519 is able to instantaneously disconnect the output from the input if the input voltage exceeds the overvoltage threshold. Additional overcurrent protection function allows turning off internal PMOS FET when the charge current exceeds current limit, which is externally selectable.

The current limit value can be modified with control logic pin to divide it by internal gain, allowing USB100 mA/500mA charging or USB/Wall adapter charging up to overcurrent threshold. At the same time, Li ion Battery voltage is continuously monitored, providing more safety during the charge.

HM9519 provides a negative going flag (FLAG) output, which alerts the system that a fault has occurred as overvoltage (power supply or battery voltage), overcurrent or thermal event.

Features

- Overvoltage Protection Up to +30V
- Fast Turn Off Time
- Very Low Current Consumption/USB Compliant
- Li ion Battery Voltage Monitoring
- Overvoltage Lockout (OVLO)
- Undervoltage Lockout (UVLO)
- Overcurrent Protection Externally Adjustable (OCP) up to 2.8A
- Thermal Shutdown
- Shutdown EN and Gain Input Pins
- Soft-Start to Eliminate Inrush Current
- Alert FLAG Output
- Compliance to IEC61000-4-2 (Level 4)
 8kV (Contact), 15kV (Air) bypassed with a 1µF or larger capacitor.
- ESD Ratings: Machine Model = B

Human Body Model = 2

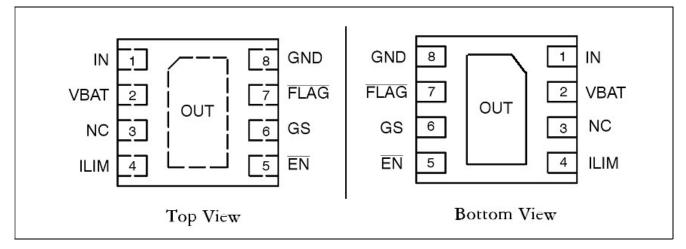
- 8 Lead DFN 2.2x2 mm Package
- These are Pb-Free Devices



Application

- USB Devices
- Mobile Phones
- Peripheral
- Personal Digital Applications
- MP3 Players

Pin Configuration



Pin Function

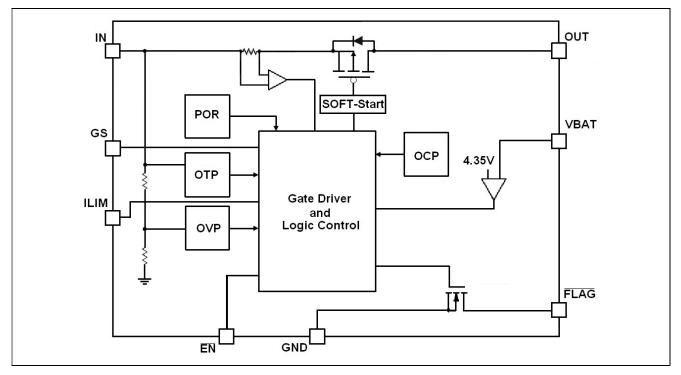
Pin No.	Name	Туре	Description		
			Input Voltage Pin. This pin is connected to the power supply: Wall Adapter		
1	IN	POWER	or USB. A 1µF low ESR ceramic capacitor, or larger, must be connected		
			between this pin and GND.		
2	V	INPUT	Li ion Battery voltage sense pin. A serial resistor must be placed between		
2	V _{BAT}	INPUT	this pin and positive pin of the battery pack.		
3	NC	OUTPUT	Not Connected.		
			Current Limit Pin. This pin provides the reference, based on the internal		
4	I_{LIM}	OUTPUT	band-gap voltage reference, to limit the overcurrent, across internal		
4			PMOSFET, from IN to OUT. A 1% tolerance, or better, resistor shall be		
			used to get the highest accuracy of the overcurrent limit.		
			Enable Mode Pin. The device enters in shutdown mode when this pin is tied		
5			to a high level. In this case the output is disconnected from the input. The		
5	EN	INPUT	state of this pin does not have an impact on the fault detection of the FLAG		
			pin.		
			Gain Select Pin. When the GS pin is tied to 0 level, the Overcurrent		
6	6 GS INPUT threshold is defined by Ilimit setting. See logic table. When C		threshold is defined by Ilimit setting. See logic table. When GS pin is tied		
	to high, the Overcurrent threshold is set to Ilimit/GS.				
7	FLAG	OUTPUT	Fault Indication Pin. This pin allows an external system to detect fault		



			condition. The FLAG pin goes low when input voltage is below UVLO			
			threshold, exceeds OVLO threshold, charge current from wall adapter to			
			battery exceeds programmed current limit, Li ion Battery voltage (4.3V) is			
	exceeded or internal temperature exceeds thermal shutdown limit. Si					
	FLAG pin is open drain functionality, an external pull-up resistor to					
			VBattery must be added ($10k\Omega$ minimum value).			
8	GND	POWER	Ground.			
			Output Voltage Pin. This pin follows IN pin when "no input fault" is			
9	OUT	OUTPUT	detected. The output is disconnected from the Vin power supply when			
9	OUT		voltage, current or thermal fault events are detected. A $1\mu F$ low ESR			
			ceramic capacitor, or larger, must be connected between this pin and GND.			

NOTE: Pin out provided for concept purpose only and might change in the final product.

Block Diagram





Functional Description

Operation

The HM9519 is an integrated IC which offers a complete protection of the portable devices during the Li ion battery charge.

First, the input pin is protected up to +30V, protecting the down stream system (charger, transceiver, system...) against the power supply transients such as inrush current or defective functionality. Additional protection level is offered with the overcurrent block which eliminates current peak or opens the charge path if an overcurrent default appears.

More of that, the battery voltage is monitored all along the input power supply is connected, allowing to open charge path if Li ion battery voltage exceeds 4.3V, caused by CCCV charger or battery pack fault.

The integrated pass element (PMOS FET) is sized to support very high charge DC current up to 2.3A. The overcurrent threshold can be externally adjusted with a pull-down resistor and gain select pin is available to divide current limit threshold with internal fixed gain. Allowing to adjust with logic pin the overcurrent threshold if USB/500mA or WA/1.5A is detected, without changing R_{ILIM} resistor, in example.

Undervoltage, Overvoltage, Overcurrent and thermal faults are signalized thanks to the open drain \overline{FLAG} pin, by pulling its down.

Undervoltage Lockout (UVLO)

To ensure proper operation under any conditions, the device has a built–in undervoltage lock out (UVLO) circuit. During Vin positive going slope, the output remains disconnected from input until Vin voltage is above 1.85V plus hysteresis nominal. This circuit has a 80mV hysteresis to provide noise immunity to transient condition.

Overvoltage Lockout (OVLO)

To protect connected systems on Vout pin from overvoltage, the device has a built-in overvoltage lock out (OVLO) circuit. During overvoltage condition, the output remains disabled as long as the input voltage exceeds this threshold.

FLAG output is tied to low as long as Vin is higher than OVLO. This circuit has a 100mV hysteresis to provide noise immunity to transient conditions.

FLAG Output

HM9519 provides a FLAG output, which alerts external systems that a fault has occurred.

This pin is tied to low as soon as the OVLO, OV_{BAT} , I_{OCP} or internal temperature thresholds are exceeded and remains low until between minimum driving voltage and UVLO threshold. When Vin level recovers normal condition, FLAG is held high. The pin is an open drain output, thus a pull up resistor (typically $1M\Omega$ – Minimum $10 \text{ k}\Omega$) must be provided to Vcc. FLAG pin is an open drain output, which is able to support 1mA maximum.

EN Input

To enable normal operation, the $\overline{\text{EN}}$ pin shall be forced to low or connected to ground. A high level on the pin, disconnects OUT pin from IN pin. $\overline{\text{EN}}$ does not overdrive a UVLO or OVLO fault.



Overcurrent Protection (OCP)

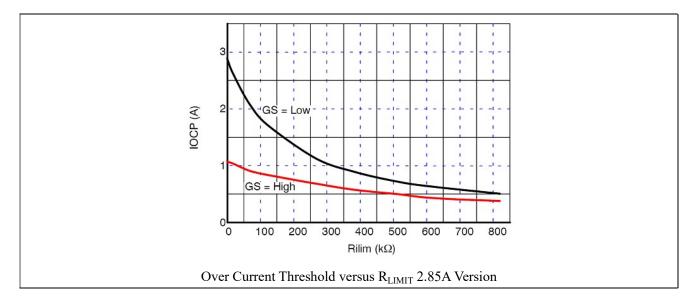
This device integrates the overcurrent protection function, from wall adapter to battery. That means the current across the internal PMOS is regulated and cut when the value, set by external RSEL resistor, exceeds I_{LIM} longer than t_{REG} .

An internal resistor is placed in series with the pin allowing to have a maximum OCP value when I_{LIM} pin is directly connected to GND.

By adding external resistors in series with ILIM and GND, the OCP value is decreased.

An additional logic pin, GS (gain select), is very useful in case of different charge rate is necessary (Wall adapter and USB, for example).

By setting GS to 0.4V, overcurrent thresholds are depending on R select resistor, which is connect between pin 4 and GND. When the GS pin is tied to 1.2V (high logic level) the preselected current limit is divided by 2.55. Thanks to this option, both fast charge or USB charge areauthorized with the same device.



Typical RLIM calculation is following: $R_{LIM} (k\Omega) = 532 / I_{OCP} - 180$

During overcurrent event, charge area is opened and \overline{FLAG} output is tied to low, allowing the μ Controller to take into account the fault event and then open the charge path.

At power up (accessory is plugged on input pins), the current is limited up to I_{LIM} during 1.8ms (typical), to allow capacitor charge and limit inrush current. If the I_{LIM} threshold is exceeded over 1.8ms, the device enter in OCP burst mode until the overcurrent event disappears.

V_{BAT} Sense

The connection of the V_{BAT} pin to the positive connection of the Li ion battery pack allows preventing overvoltage transient, greater than 4.35V. In case of wrong charger conditions, the PMOS is then opened, eliminating Battery pack over voltage which could create safety issues and temperature increasing.

The 4.35V comparator has a 150mV built-in hysteresis.

More of that, deglitch function of 2ms is integrated to prevent voltage transients on the Battery voltage. If the battery over voltage condition exceeds deglitch time, the charge path is opened and \overline{FLAG} pin is tied to low level



until the V_{BAT} is greater than 4.35V-hysteresis.

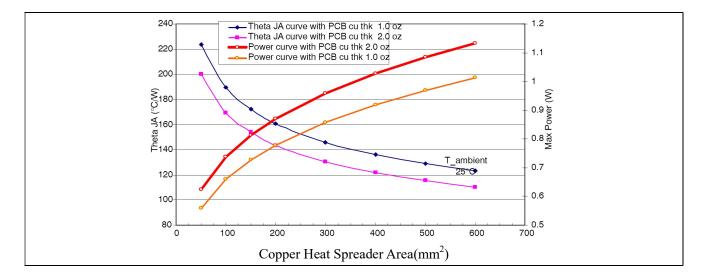
At wall adapter insertion, and if the battery is fully charged, V_{bat} comparator stays locked until battery needs to be recharged (4.2V typ-4.1V min).

A serial resistor has to be placed in series with Vbat pin and battery connection, with a $200k\Omega$ recommended value.

PCB Recommendations

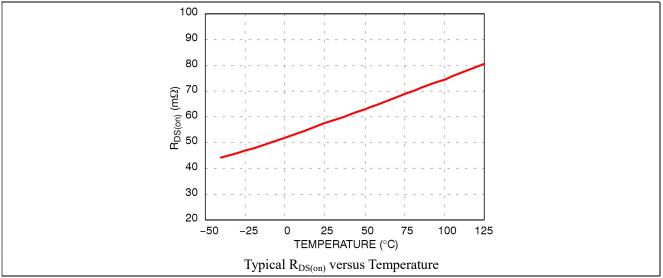
The HM9519 integrates low $R_{DS(on)}$ PMOS FET, nevertheless PCB layout rules must be respected to properly evacuate the heat out of the silicon. The DFN PAD1 corresponds to the PMOS drain so must be connected to OUT plane to increase the heat transfer. Of course, in any case, this pad shall be not connected to any other potential.

Following figure shows package thermal resistance of a DFN 2.2x2 mm.



Internal PMOS FET

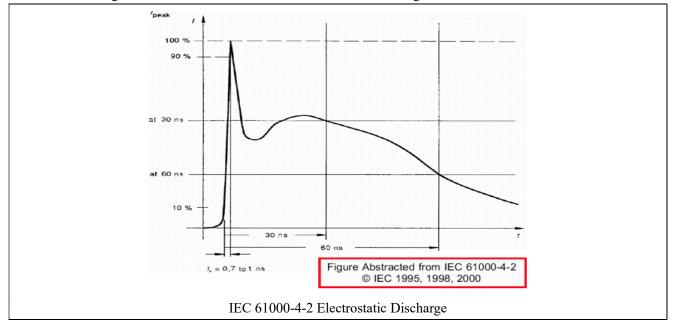
HM9519 includes an internal PMOS FET to protect the systems, connected on OUT pin, from positive over-voltage. Regarding electrical characteristics, the R_{DSon} , during normal operation, will create low losses on V_{out} pin versus Vin, thanks to very low R_{DSon} .





ESD Tests

HM9519 fully support the IEC61000-4-2, level 4 (Input pin, 1 μ F mounted on board). That means, in Air condition, Vin has a ± 15 kV ESD protected input. In Contact condition, Vin has ± 8 kV ESD protected input. Please refer to Figure 15 to see the IEC 61000-4-2 electrostatic discharge waveform.



Parameter	Symbol	Value	Unit
Minimum Voltage (IN to GND)	Vmin _{in}	-0.3	V
Minimum Voltage (All others to GND)	Vmin	-0.3	V
Maximum Voltage (IN to GND)	Vmax _{in}	30	V
Maximum Voltage (All others to GND)	Vmax	7.0	V
Maximum DC Current from Vin to Vout (PMOS)	Imax	3.4	А
Thermal Resistance, Junction-to-Air (without PCB area)	$R_{\theta JA}$	190	°C/W
Operating Ambient Temperature Range	T _A	-40 to +85	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Junction Operating Temperature	TJ	150	°C
ESD Withstand Voltage (IEC 61000-4-2)		15 Air, 8.0 Contact	kV
Human Body Model (HBM), Model = 2 (Note 1)	V_{esd}	2000	V
Machine Model (MM) Model = B (Note 2)		200	V
Latchup	LU	Class 1	-
Moisture Sensitivity	MSL	Level 1	-

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Human Body Model, 100pF discharged through a $1.5k\Omega$ resistor following specification JESD22/A114.

2. Machine Model, 200pF discharged through all pins following specification JESD22/A115.



Electrical Characteristics

(Min/Max limits values ($-40^{\circ}C < T_A < +85^{\circ}C$) and Vin = +5.0V. Typical values are $T_A = +25^{\circ}C$, unless otherwise noted.)

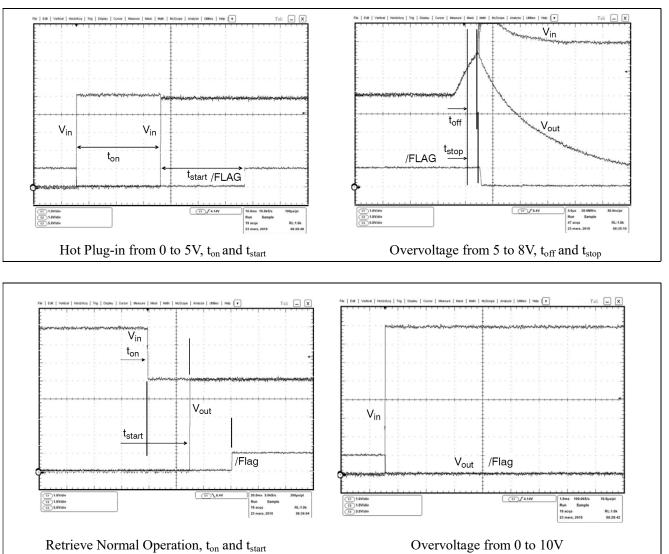
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Voltage Range	V _{in}		1.2		28	V
Undervoltage Lockout Threshold	UVLO	V _{in} falls down UVLO threshold	1.75	1.85	1.9	v
Undervoltage Lockout Hysteresis	UVLO _{hyst}			80	100	mV
Overvoltage Lockout Threshold	OVLO	V _{in} rises up OVLO threshold	6.90	7.20	7.50	v
Overvoltage Lockout Hysteresis	OVLO _{hyst}			100	150	mV
Vin versus Vout Resistance	R _{DS(on)}	V_{in} = 5 V, Enable Mode, Load Connected to V_{out}		40	90	mΩ
Supply Quiescent Current	Idd	No Load		40	120	μΑ
Disable Mode	Idd _{dis}	$\overline{\mathrm{EN}} = 1.2\mathrm{V}$		38	100	μΑ
Overcurrent Threshold	I _{ocp}	Vin = 5V, \overline{EN} = low, Load Connected to V_{out} , $R_{ilim} = 0$ ohms, 1A/µs, GS = 0.4V	2.30	2.85	3.40	А
Overcurrent Response	I _{reg}	$1 \text{ A}/\mu \text{s}, \text{ GS} = \text{low}, \text{ I}_{\text{lim}} = 1.51 \text{ A}$		5.0		%
Current Limit Gain	GS _{value}	GS = 1.2V		2.55		
Battery Overvoltage Threshold	OV _{BAT}	0°C to 85°C	4.3	4.35	4.4	v
Battery Overvoltage Hysteresis	OV _{HYS}	0°C to 85°C	100	150	200	mV
V _{BAT} Pin Leakage	VBAT _{LEAK}				20	nA
V_{BAT} Deglitch Time	VBAT _{DEG}	$V_{BAT} > OV_{BAT}$	0.2	2.0	4.0	ms
FLAG Output Low Voltage	Vol _{flag}	V _{in} > OVLO Sink 1 mA on FLAG pin			400	mV
FLAG Leakage Current	FLAG _{leak}	$\overline{\text{FLAG}}$ level = 5V		10		nA
EN Voltage High	V _{ih}	V_{in} from 3.3V to 5.25V	1.2			V
EN Voltage Low	V _{il}	V_{in} from 3.3V to 5.25V			0.4	V
EN Leakage Current	EN _{leak}	$\overline{\text{EN}} = 5.5 \text{V} \text{ or GND}$		200		nA
GS Voltage High	V _{ih}	V_{in} from 3.3 V to 5.25 V	1.2			V
GS Voltage Low	V _{il}	V_{in} from 3.3 V to 5.25 V			0.4	V
GS Leakage Current	GS _{leak}	$\overline{\text{EN}} = 5.5 \text{V} \text{ or GND}$		200		nA
TIMINGS						
Start Up Delay	t _{on}	From $V_{in} > UVLO$ to $V_{out} = 0.8 x V_{in}$	15	30	45	ms
FLAG going up Delay	t _{start}	From $V_{out} > 0.2 x V_{in}$ to $\overline{FLAG} = 1.2 V$	15	30	45	ms
Rearming Delay	t _{REARM}	OCP Active	15	30	45	ms



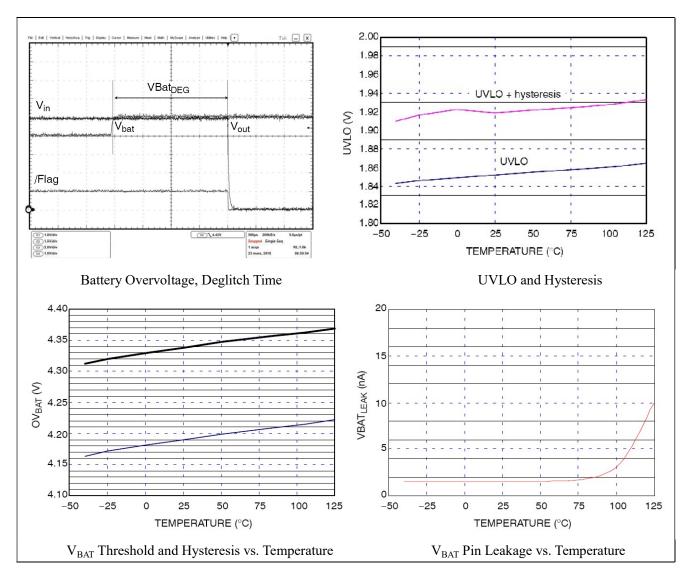
Overcurrent Regulation Time	t _{REG}	OCP Active	1.2	1.8	3.0	ms	
Output Turn Off Time	t _{off}	From V_{in} > OVLO to $V_{out} \le 0.3 V$, V_{in} increasing from 5V to 8V at $3V/\mu s$.		1.5	5.0	μs	
Alert Delay	t _{stop}	$\label{eq:rom_vin} \begin{split} From \ V_{in} &> OVLO \ to \ \overline{FLAG} \leq 0.4V \\ V_{in} \ increasing \ from \ 5V \ to \ 8 \ V \ at \ 3 \ V/\mu s \end{split}$		1.5		μs	
Disable Time	t _{dis}	From $\overline{\text{EN}}$ 0.4 to 1.2V to $V_{\text{out}} \le 0.3$ V		3.0		μs	
TIMINGS	TIMINGS						
Thermal Shutdown Temperature	T _{sd}			150		°C	
Thermal Shutdown Hysteresis	Tsd _{hyst}			30		°C	

NOTE: Electrical parameters are guaranteed by correlation across the full range of temperature.

Typical Operating Characteristics



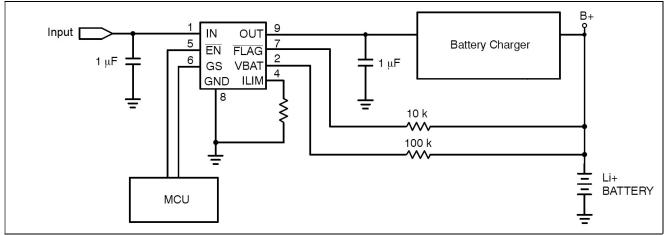




HM-)%

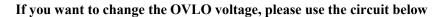
Application Circuits

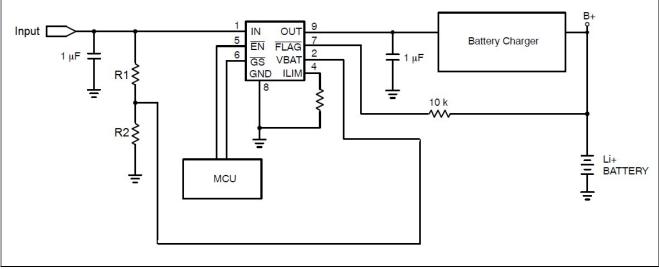
Typical circuit



*: This circuit is for reference only.







*NOTE:

Typical OVLO voltage calculation is following:

OVLO=4.35*(R1+R2)/R2

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Overvoltage Lockout	OVLO	R1=80K±1%, R2=1M±1%	4.64	4.7	4.76	V
Threshold	0.10					



Package Dimension

